

1. General description

40A 650V Trench Fieldstop IGBT with anti-parallel diode in TO3PF package. The WeEn WG40N65DFJ uses advanced field stop technology. This device is ideal for Motor Driver and PFC.



2. Features and benefits

- Advanced Trench Fieldstop technology
- Very soft, fast recovery anti-parallel diode
- High speed switching
- EMI Improved Design

3. Applications

- Motor driver
- PFC

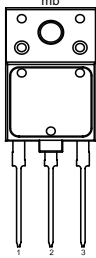
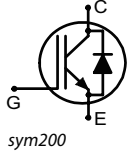
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Notes	Value			Unit	
V_{CE}	Collector-emitter voltage, $T_j \geq 25\text{ °C}$		650			V	
I_C	DC collector current, limited by $T_{j(max)}$ $T_C = 100\text{ °C}$		15			A	
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}; I_C = 40\text{ A}; T_j = 25\text{ °C}$		-	1.5	1.95	V

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		 sym200
2	C	collector		
3	E	emitter		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WG40N65DFJ	TO3PF	WG40N65DFJQ	Tube	30	SOT1293	16-Mar-2006

7. Marking

Table 4. Marking codes

Type number	Marking codes
WG40N65DFJ	WG40N 65DFJ

8. Limiting values

Table 5. Limiting values

Symbol	Parameter	Notes	Value	Unit
V_{CE}	Collector-emitter voltage, $T_j \geq 25\text{ °C}$		650	V
I_C	DC collector current, limited by $T_{j(max)}$ $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$		31 15	A
$I_{C(puls)}$	Pulsed collector current, t_p limited by $T_{j(max)}$		120	A
-	Turn off safe operating area $V_{CE} \leq 600\text{ V}$, $T_j \leq 125\text{ °C}$, $t_p = 1\text{ }\mu\text{s}$		120	A
I_F	Diode forward current, limited by $T_{j(max)}$ $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$		25 12	A
$I_{F(puls)}$	Diode pulsed current, t_p limited by $T_{j(max)}$		40	A
V_{GE}	Gate-emitter voltage		± 20	V
P_{tot}	Power dissipation $T_C = 25\text{ °C}$ Power dissipation $T_C = 100\text{ °C}$		66 26	W
T_{stg}	Storage temperature		-55 to 150	°C
T_j	Operating junction temperature		-55 to 150	°C
-	Peak soldering temperature		260	°C
M	Mounting Torque with washer		0.55	Nm

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-c)}$	IGBT thermal resistance from junction to case			-	1.9	-	K/W
$R_{th(j-c)}$	Diode thermal resistance from junction to case			-	3.6	-	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient			-	40	-	K/W

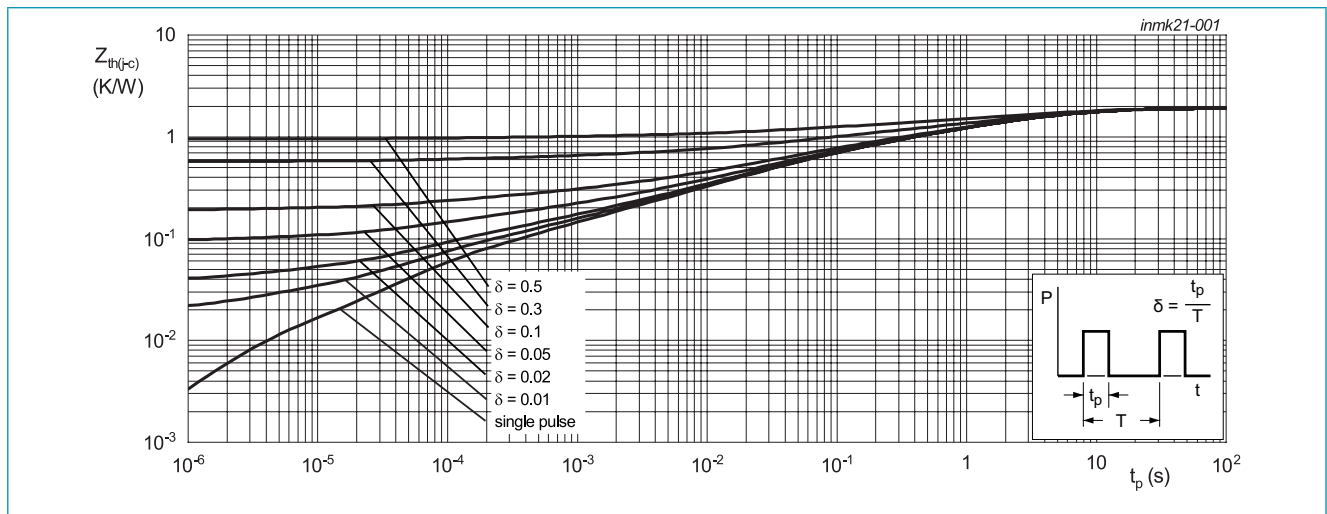


Fig. 1. Transient thermal impedance from junction to case as a function of pulse duration; IGBT

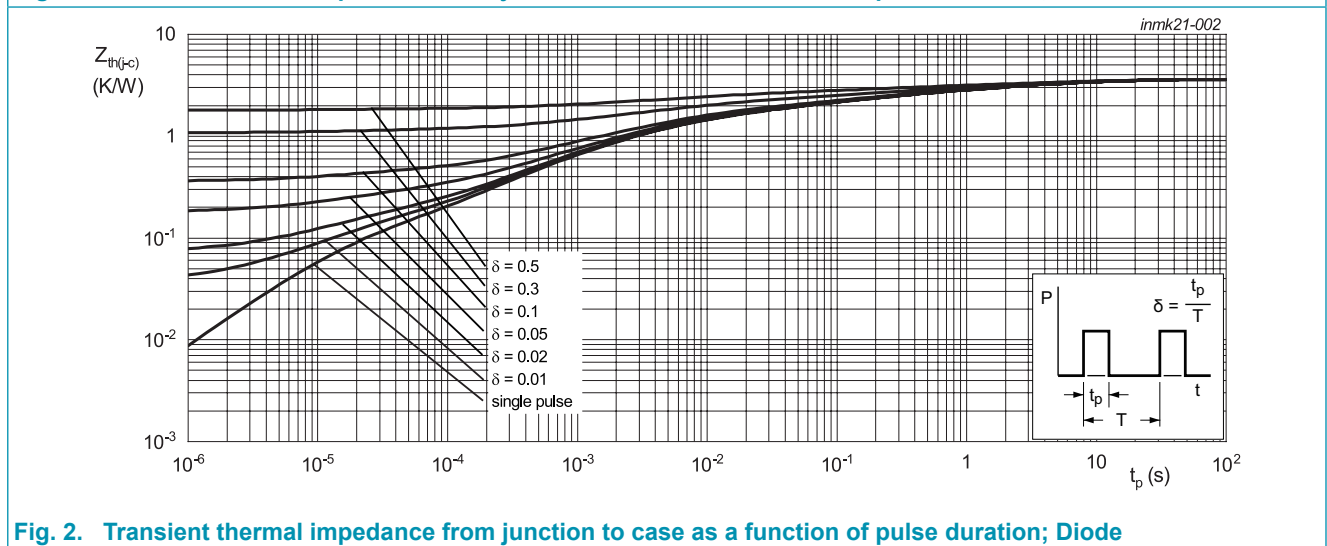


Fig. 2. Transient thermal impedance from junction to case as a function of pulse duration; Diode

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
BV_{CES}	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}; I_C = 50\ \mu\text{A}$		650	-	-	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}; I_C = 40\text{ A}; T_j = 25\text{ }^\circ\text{C}$		-	1.5	1.95	V
		$V_{GE} = 15\text{ V}; I_C = 40\text{ A}; T_j = 150\text{ }^\circ\text{C}$		-	1.8	-	V
V_F	Diode forward voltage	$V_{GE} = 0\text{ V}; I_F = 10\text{ A}; T_j = 25\text{ }^\circ\text{C}$		-	1.24	-	V
		$V_{GE} = 0\text{ V}; I_F = 10\text{ A}; T_j = 150\text{ }^\circ\text{C}$		-	1.1	-	V
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C = 1\text{ mA}; V_{CE} = V_{GE}$		4.2	5.2	6.2	V
I_{CES}	Zero gate voltage collector current	$V_{CE} = 650\text{ V}; V_{GE} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	-	10	μA
		$V_{CE} = 650\text{ V}; V_{GE} = 0\text{ V}; T_j = 150\text{ }^\circ\text{C}$		-	-	1	mA
g_{fs}	Transconductance	$V_{CE} = 20\text{ V}; I_C = 40\text{ A}$		-	20	-	S
Dynamic characteristics							
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$		-	1595	-	pF
C_{oes}	Output capacitance			-	79	-	pF
C_{res}	Reverse transfer capacitance			-	49	-	pF
Q_G	Gate charge	$V_{CC} = 520\text{ V}; I_C = 40\text{ A}; V_{GE} = 0\text{ to }15\text{ V}; T_j = 25\text{ }^\circ\text{C}$		-	173	-	nC

11. Switching Characteristics

Table 8. Switching Characteristics, Inductive Load

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
IGBT characteristics							
$t_{d(on)}$	Turn-on delay time	$T_J = 25\text{ }^\circ\text{C};$ $V_{CC} = 400\text{ V}; I_C = 40\text{ A}; V_{GE} = 15\text{V} / 0\text{V};$ $R_G = 10\text{ }\Omega$		-	36	-	nS
t_r	Rise time			-	58	-	nS
$t_{d(off)}$	Turn-off delay time			-	250	-	nS
t_f	Fall time			-	49	-	nS
E_{on}	Turn-on energy			-	1.7	-	mJ
E_{off}	Turn-off energy			-	1	-	mJ
E_{ts}	Total switching energy			-	2.7	-	mJ
$t_{d(on)}$	Turn-on delay time	$T_J = 150\text{ }^\circ\text{C};$ $V_{CC} = 400\text{ V}; I_C = 40\text{ A}; V_{GE} = 15\text{V} / 0\text{V};$ $R_G = 10\text{ }\Omega$		-	35	-	nS
t_r	Rise time			-	60	-	nS
$t_{d(off)}$	Turn-off delay time			-	278	-	nS
t_f	Fall time			-	100	-	nS
E_{on}	Turn-on energy			-	2.4	-	mJ
E_{off}	Turn-off energy			-	1.4	-	mJ
E_{ts}	Total switching energy			-	3.8	-	mJ
Diode characteristics							
t_{rr}	Reverse recovery time	$T_J = 25\text{ }^\circ\text{C};$ $V_R = 400\text{ V}; I_F = 30\text{ A}; dI_F/dt = 500\text{ A/us}$		-	81	-	nS
Q_r	Reverse recovery charge			-	646	-	nC
I_{RM}	Reverse recovery peak current			-	16	-	A
t_{rr}	Reverse recovery time	$T_J = 150\text{ }^\circ\text{C};$ $V_R = 400\text{ V}; I_F = 30\text{ A}; dI_F/dt = 500\text{ A/us}$		-	136	-	nS
Q_r	Reverse recovery charge			-	1628	-	nC
I_{RM}	Reverse recovery peak current			-	24	-	A

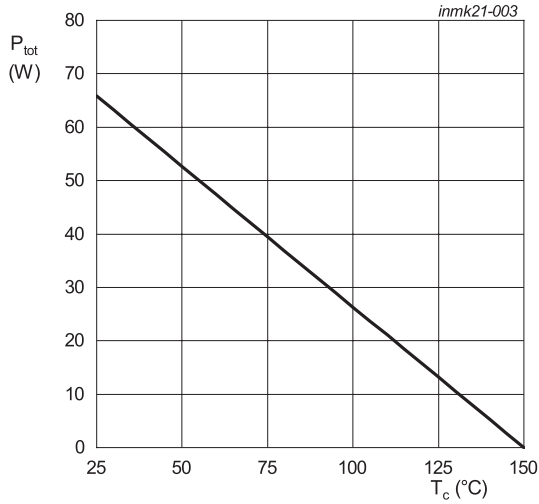


Fig. 3. Power dissipation as a function of case temperature

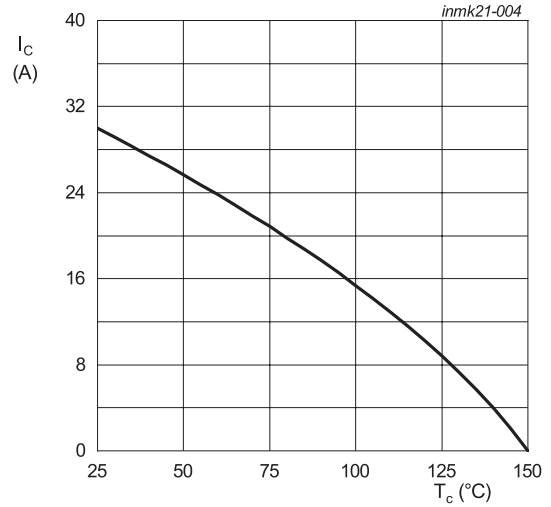


Fig. 4. Collector current as a function of case temperature
 $V_{GE} = 15 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$

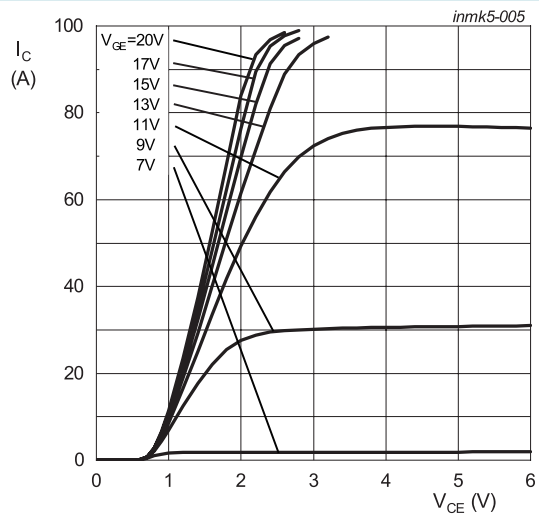


Fig. 5. Typical output characteristic
 $T_j = 25 \text{ }^\circ\text{C}$

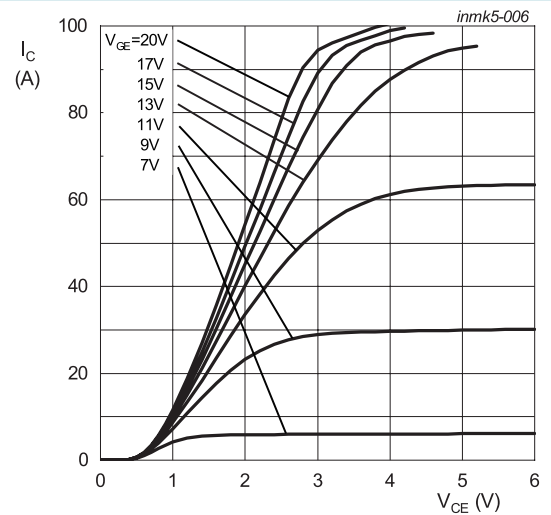
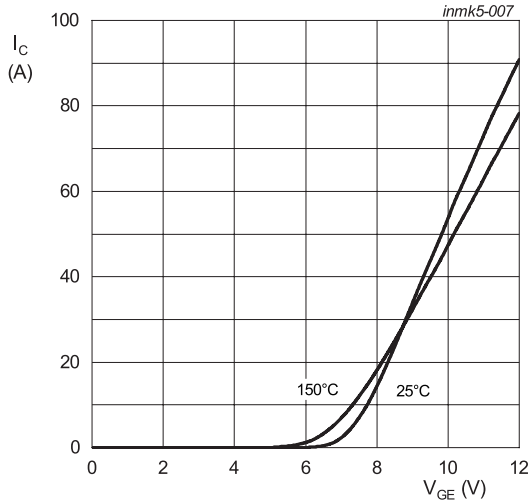
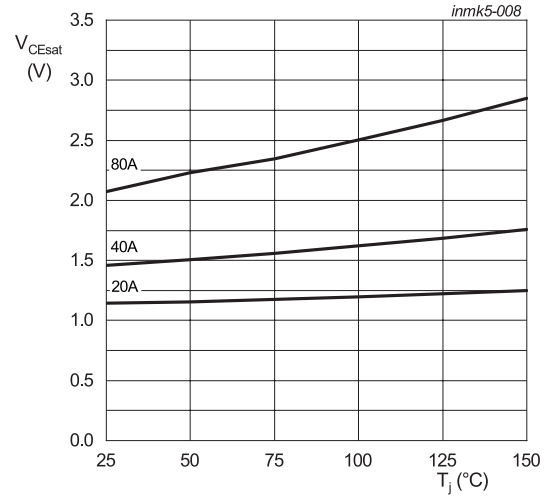


Fig. 6. Typical output characteristic
 $T_j = 150 \text{ }^\circ\text{C}$



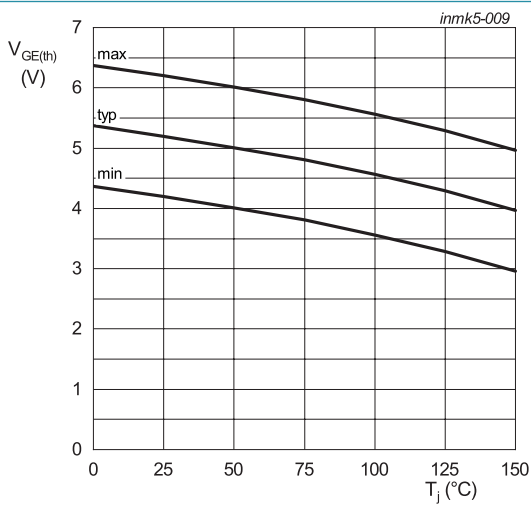
$V_{CE} = 20\text{ V}$

Fig. 7. Typical transfer characteristic



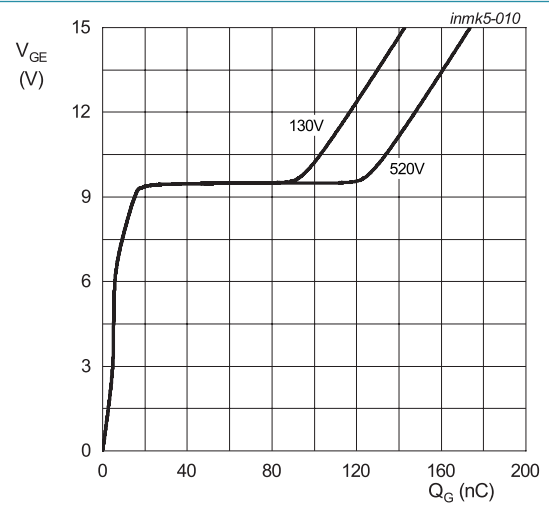
$V_{GE} = 15\text{ V}$

Fig. 8. Typical collector-emitter saturation voltage as a function of junction temperature



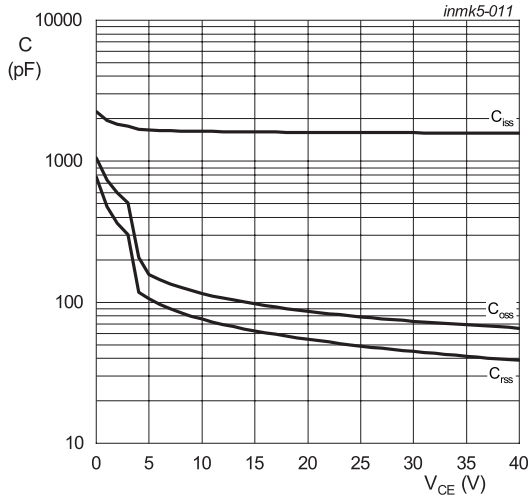
$I_C = 1\text{ mA}$

Fig. 9. Gate-emitter threshold voltage as a function of junction temperature



$I_C = 40\text{ A}$

Fig. 10. Typical gate charge



$V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig. 11. Typical capacitance as a function of collector-emitter voltage

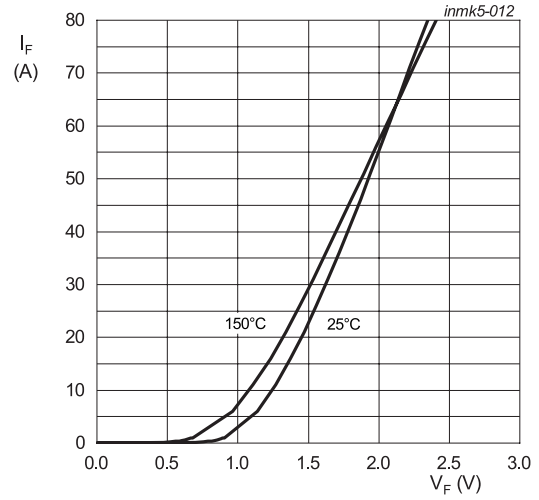
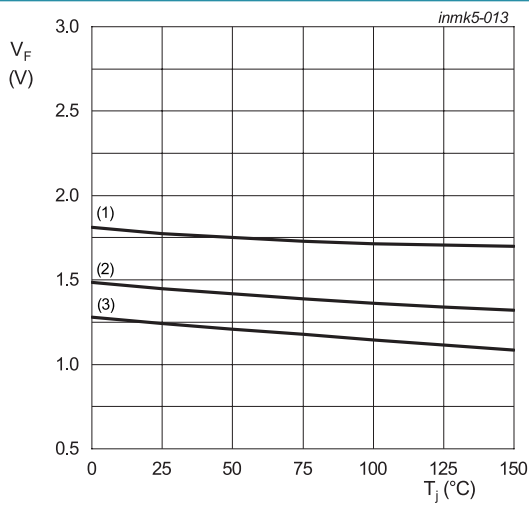
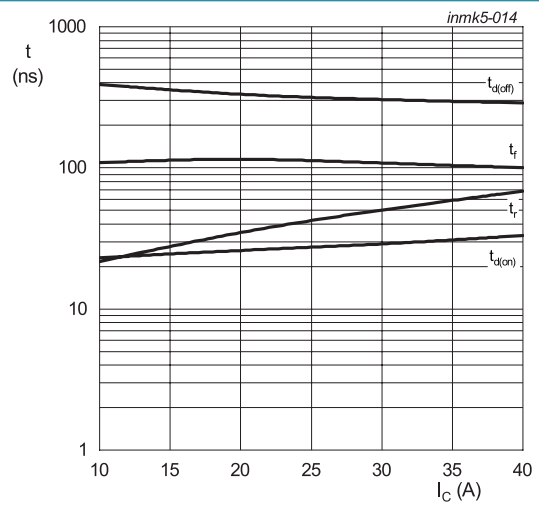


Fig. 12. Typical diode forward current as a function of forward voltage



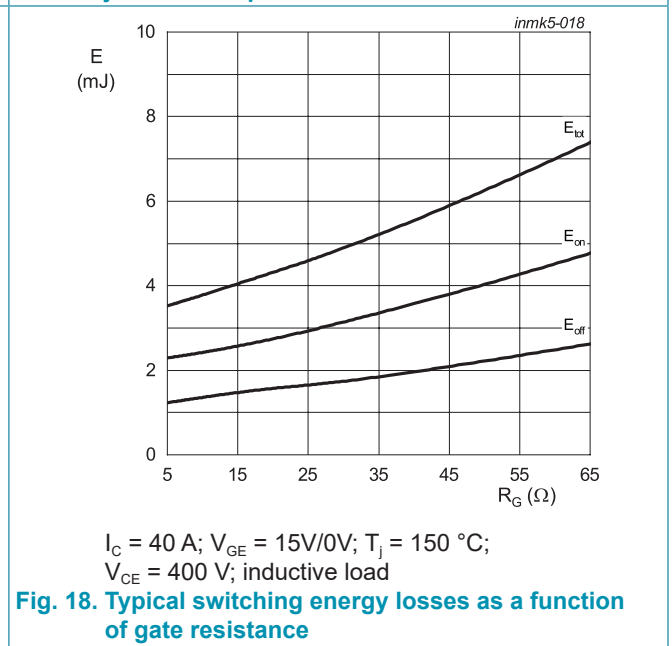
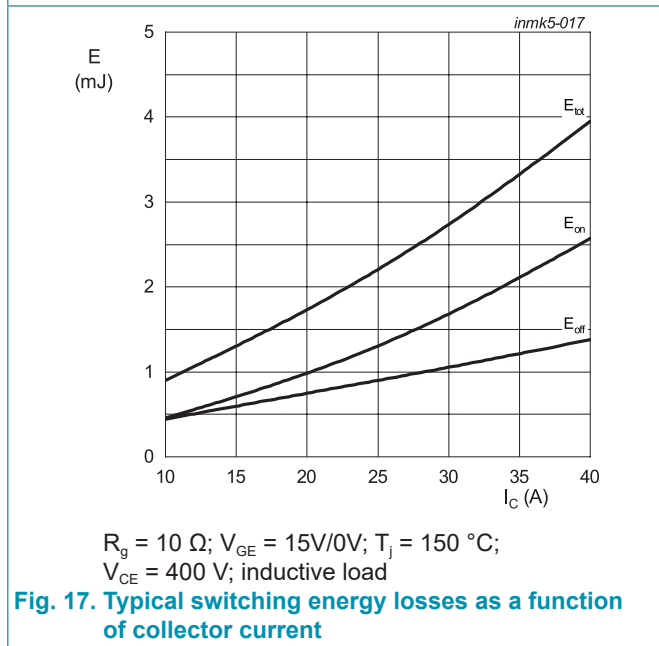
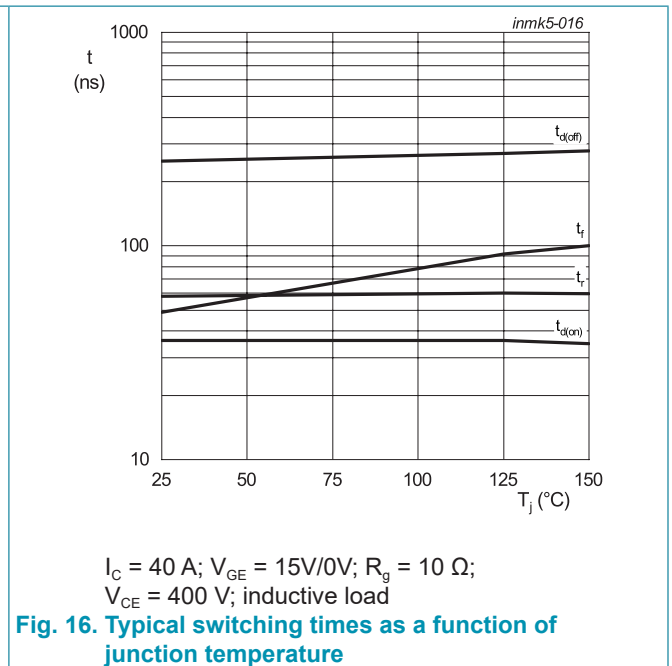
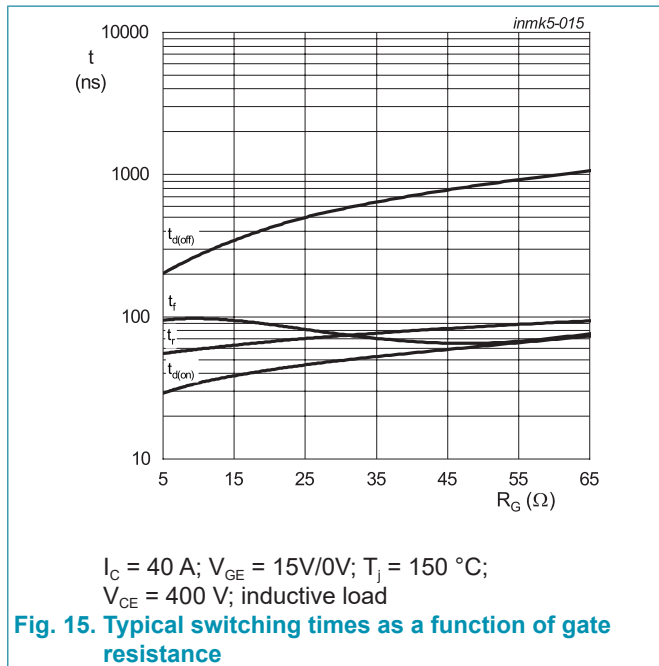
- (1) $I_F = 40 \text{ A}$
- (2) $I_F = 20 \text{ A}$
- (3) $I_F = 10 \text{ A}$

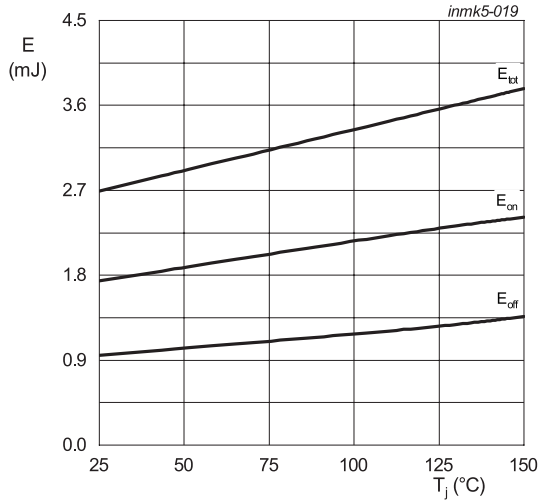
Fig. 13. Typical diode forward voltage as a function of junction temperature



$R_g = 10 \Omega; V_{GE} = 15\text{V}/0\text{V}; T_j = 150 \text{ }^\circ\text{C};$
 $V_{CE} = 400 \text{ V};$ inductive load

Fig. 14. Typical switching times as a function of collector current





$I_C = 40\text{ A}$; $V_{GE} = 15\text{V}/0\text{V}$; $R_g = 10\ \Omega$;
 $V_{CE} = 400\text{ V}$; inductive load

Fig. 19. Typical switching energy losses as a function of junction temperature

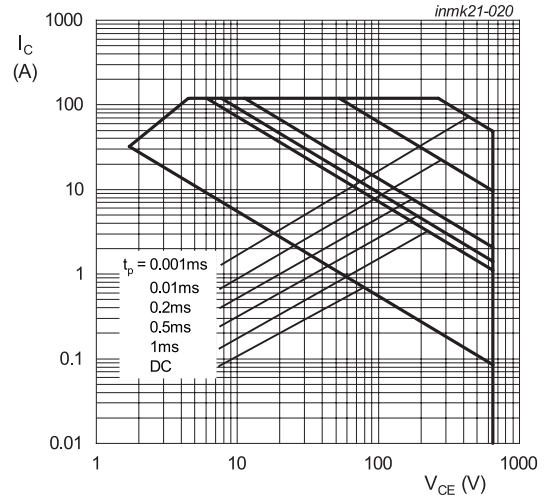


Fig. 20. Forward bias safe operating area

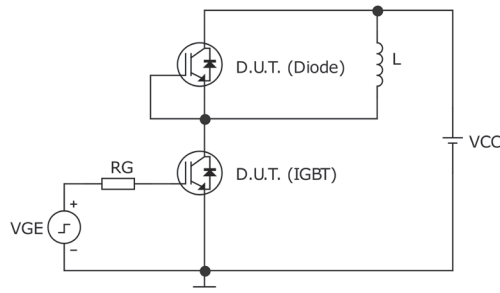


Fig. 21. Test circuit for inductive load switching

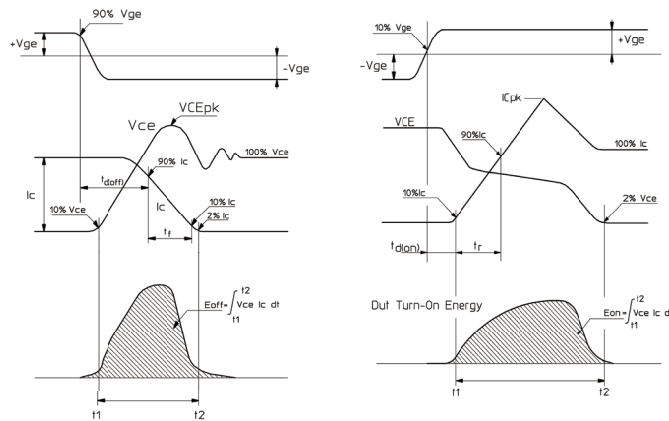
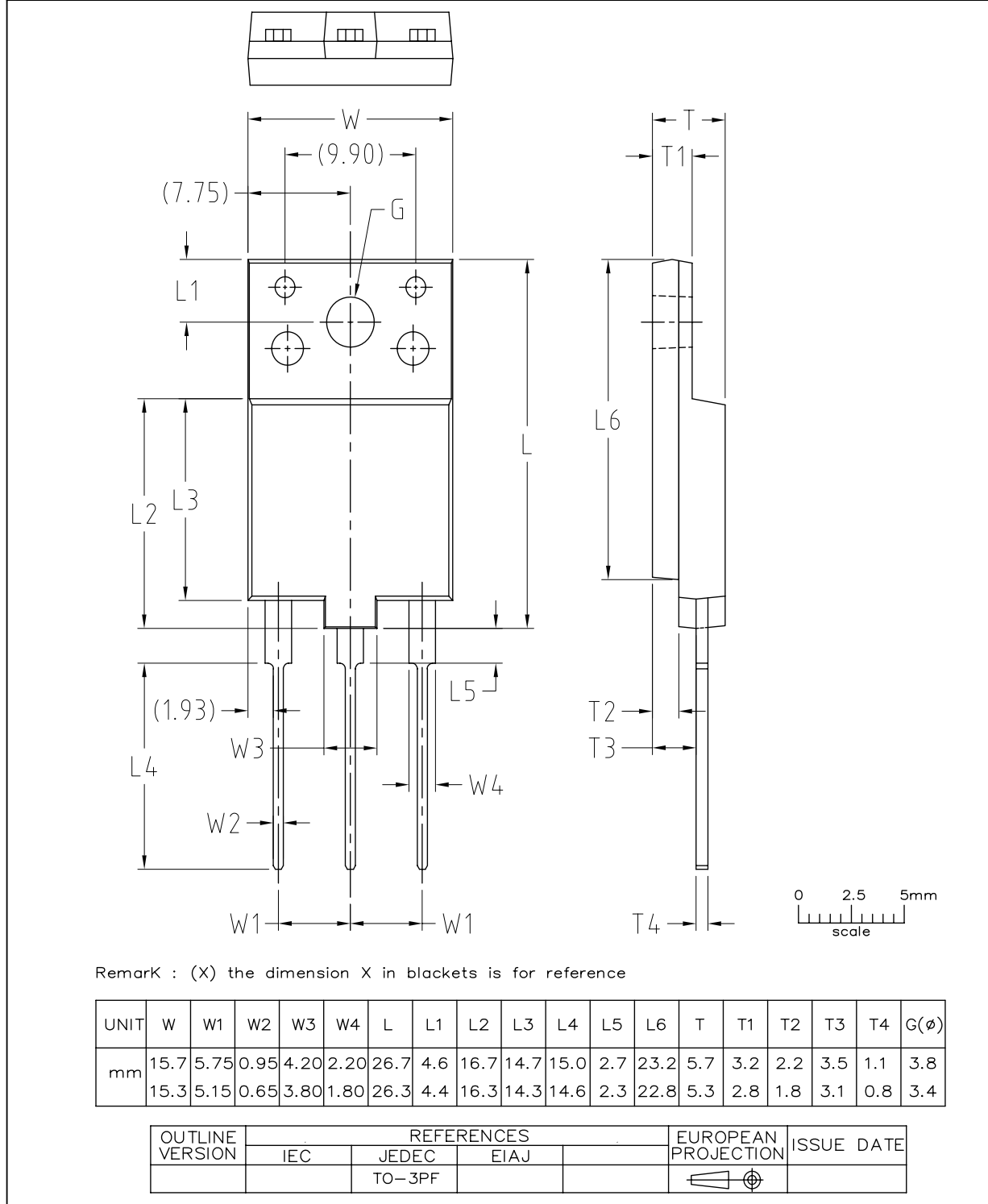


Fig. 22. Definition of switching times and losses

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'

TO3PF



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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